Transmission Phase Through Two Quantum Dots Embedded in a Four-Terminal Quantum Ring

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We use the Aharonov-Bohm e ect in a four-term inal ring based on a GaAlA sheterostructure for the measurement of the relative transmission phase. In each of the two interfering paths we induce a quantum dot. The number of electrons in the two dots can be controlled independently. The transmission phase is measured as electrons are added to or taken away from the individual quantum dots.

Two-term inal interference measurements in nanostructures do not allow the determination of the relative transmission phase due to the generalized Onsager relations [1]. In a series of recent experiments it has been dem onstrated [2, 3, 4, 5] that in a multi-term inal geom etry the relative transm ission phase can be directly observed. In the quantum rings used in these experiments, two spatially separate transmission channels interfere and the phase di erence of the corresponding transm ission amplitudes can be detected by measuring A haronov-Bohm (AB) oscillations. By using one of the two interfering paths as a reference the phase evolution in the other path can be studied, e.g. when a Coulom b blockaded quantum dot is embedded there [2]. It was found that the transmission phase changes by about across a typical C oulom b blockade resonance and regularly exhibits so-called phase lapses between resonances. Sim ilar experim ents were carried out on a K ondo-correlated system in Refs. [4] and [5]. A large number of theoretical papers (for a review see [6]) has addressed the issue of the phase lapses.

Here we investigate the phase evolution of a system of two quantum dots with negligible electrostatic interaction embedded in two arms of a four-term inal AB ring. Both arm softhe ring including the two dots can be tuned individually. As a single electron is added to either of the two quantum dots by increasing the corresponding plunger gate voltage, the observed average phase shift is about but sm aller shifts are also observed. In such a measurement one dot is kept on a conductance resonance while the phase evolution induced by tuning the other dot through a resonance is monitored. In contrast, if a single electron is added to each of the quantum dots sim ultaneously, the observed phase shift is close to zero, since the relative phase change in each arm is roughly the sam e.

The sample is a G a A IA s heterostructure containing a two-dimensional electron gas 37 nm below the surface. The lateral pattern was fabricated with the biased tip of an atom ic force m icroscope which locally oxidizes the G aA s surface. Details of this fabrication technique are described in Ref. [7]. Figure 1 (a) shows an AFM m icro-

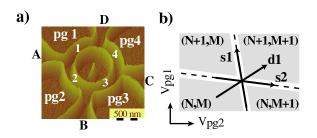


FIG.1: (a) AFM m icrograph of the ring structure. The oxide lines (bright lines) fabricated by AFM lithography lead to insulating barriers in the two-dimensional electron gas. The areas marked pg1-pg4 are used as lateral gates to tune the conductance of the four arm s of the ring and act as plunger gates for the dots. The four term inals of the ring are labeled A through D. (b) Schem atic plot of the parameter space de ned by V_{pg1} and V_{pg2} . The dashed lines mark the conductance maximum positions. A B-oscillations were measured along the arrows. N (M) denotes the electron occupation in dot 1(2) respectively.

graph of the oxidized pattern. Lateralgate electrodes labeled pgl through pg4 are used to tune the conductance in each of the four segments of the ring. All measurements were carried out at 100m K in a dilution refrigerator.

The ring was characterized in the open regime where each segment supports 2-4 lateral modes. Figure 2(a) shows a pronounced AB e ect in a local measurement setup in which the current and voltage contacts are the same two term inals of the ring [inset Fig. 2(a)]. The period $B = {}_{0}=A$ 4.8 mT is in agreement with the area A = 0.85 m² enclosed by the ring.

The non-local resistance was measured by passing a current through anm 2 and measuring the voltage drop across arm 4. This is shown in Fig.2(b). In this case the AB-oscillations constitute only 2% of the total signal. In order to maxim ize the AB signal we therefore chose a di erent arrangement [inset Fig.2(c)] similar to the one used in Ref. [2]. Here a bias voltage V_b was applied to term inal A. The lower and upper contacts (B and D) were grounded via current-voltage converters measuring the currents I_B and I_b. The non-local voltage V_{n1} was measured values of the total valu

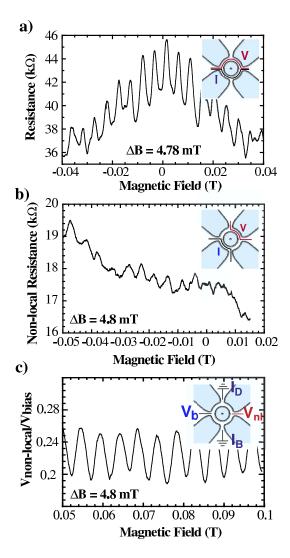


FIG.2: (a) AB-O scillations in a local measurem ent setup (see inset). (b+c) Two di erent non-local setups. The measurem ent setup shown in the inset of (c) turned out to show the largest AB-O scillations and was therefore used for the phase sensitive measurem ents.

sured at term inalC. The amplitude of the AB-oscillations in V_{n1} [Fig.2(c)] was found to be about 25% of the total signal.

W e also characterized the four arm s of the ring in the closed regime. To this end we measured the two-term inal conductance of each segment as a function of gate voltage when the arm on the opposite side was pinched-o by applying a strongly negative voltage to the corresponding plunger gate. In Fig. 3 the resulting conductance sweeps are shown. For low enough gate voltages clear C oulom b blockade oscillations are observed indicating the form ation of a quantum dot in the arm tuned.

The location of the quantum dots can be estimated from the respective lever arms to each of the gates pgl to pg4 which reveals that the dots form within the segments and not at the openings to the contacts. The lever

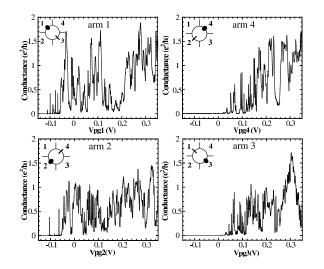


FIG.3: Coulom b blockade oscillations in the conductance through each arm of the ring measured in a two-term inal conguration. For each measured arm the opposite arm was pinched o by applying a strongly negative voltage to the corresponding gate. The schem atic at the top left in each gure depicts the measurem ent setup where the line m arks the arm which is pinched o and the black dot indicates the arm which is tuned.

arm for the gate closest to the corresponding dot is found to be $_{\rm G}$ 0:16, for the two adjacent gates the lever arm is about a factor of seven smaller and for the gate opposite the dot the lever arm is fourteen times smaller. From C oulom b blockade diam ond m easurem ents we nd a typical C oulom b charging energy of 1 m eV, which corresponds roughly to the area of a single segment in a disc-capacitor m odel.

In the following experiments we choose a regime where arm 1 and 2 are in the C oulom b blockade regim e w hile the other two arms are left open and contain several lateral modes. We study a region in the plane de ned by V_{bg1} and V_{pq2} close to a setting where both dots are tuned to a conductance maximum. This is shown schematically in Fig.1 (b) where the dashed lines m ark the C oulom b peak positions. The num bers in brackets indicate the electron occupation of the two dots. In our measurem ents we st keep one dot on a conductance maximum while stepping through a conductance peak in the other dot (traces sl and s2 indicated by the arrows). At the same time we detect the AB-oscillations in the non-local voltage for each value of the gate voltage. Figure 4 (a) shows an example where dot 2 is tuned along trace s2. The current signals on the left of the gure show a peak in the current I, ie. the current in the term inal closer to the tuned dot. The current I_p shows a weak monotonous dependence on pg2, as expected. In the main part of the gure on the right, AB-oscillations in the non-local voltage as a function of magnetic eld are shown for selected gate voltages (dashed lines in the left part of the gure). We nd that for very small magnetic elds the amplitude of the

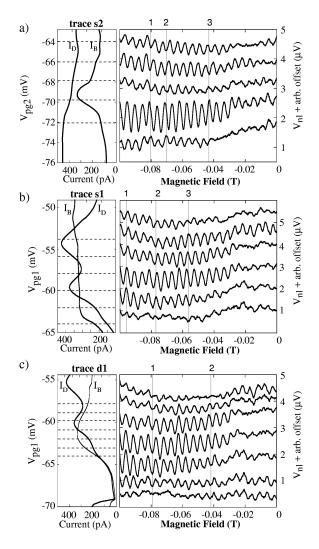


FIG.4: Currents $I_{\rm B}$ and $I_{\rm D}$ and AB-oscillations in the non-local voltage $V_{\rm n1}$ as a function of plunger gate voltages tuned along traces s2 (a), s1 (b) and d1 (c). The AB-oscillations are taken at the gate values indicated by the dashed lines. The thin vertical lines are shown only as a guide to the eye in order to visualize the phase shift m ore clearly.

AB-oscillations is suppressed and it is di cult to make a statem ent about a phase change between the curves. The num bered thin vertical lines are a quide to the eye and connect maxim a in the upperm ost trace with minim a in the lowest trace. This indicates a phase shift by about as expected for the phase accumulation over a single isolated resonance [2, 6]. W hile the shift is continuous and positive (from top to bottom) for line 1 we nd a slightly sm aller shift for line 2 over the whole range of sweeps. A shift by takes place over the middle three curves. A change in phase or frequency for di erent values of the magnetic eld could mean that in a sem iclassical picture di erent paths around the ring contribute to the interference signal as the magnetic eld is tuned. This illustrates that from our data a magnetic eld independent AB-phase cannot be unambiguously de ned.

A long trace s1 [Fig. 4(b)] dot 1 is tuned while dot 2 is kept on a conductance resonance. Here, current I_{B} shows the expected at behavior, but we observe a double peak structure in current I_D . The phase change has the opposite sign compared to trace s2. For the vertical line 3 we nd almost the expected phase change of For lines 1 and 2 the phase change is, however, sm aller. W hile the magnetic eld dependence of the phase needs further investigation we do nd that the relative change of the transm ission phase in both dots is the same as an electron is added to them . This means that the interference patterns are shifted in opposite directions. In order to verify this we show the results for a sweep along the diagonal trace d1 where two electrons are added simultaneously to both dots [Fig 4 (c)]. For magnetic elds above 50 m T we nd that the phase change over the conductance resonance is indeed 0 = as expected (see vertical line 1). However, we again nd that deviations from this behavior occur for sm all magnetic elds where nd a sm all shift of the phase (vertical line 2). we

The design and fabrication process of our samples is di erent from the experiment by Schuster et al. [2]. In contrast to their experiment we have a second dot in the reference arm of the interferom eter which gives us additional control of the relative phase change. Our ndings indicate that the shift of the transm ission phase of both dots has the same sign when they are tuned over a conductance resonance and the electron occupation is increased. In agreement with our expectation, we nd a negligible shift for trace d1 where the phase di erence between the arm s of the ring remains constant.

In conclusion, we have demonstrated that the phase evolution can be measured with individual control over the electron occupancy in each dot. W hile the general features are understood qualitatively, further work is needed to explain magnetic eld dependent deviations from the theoretically expected phase changes.

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